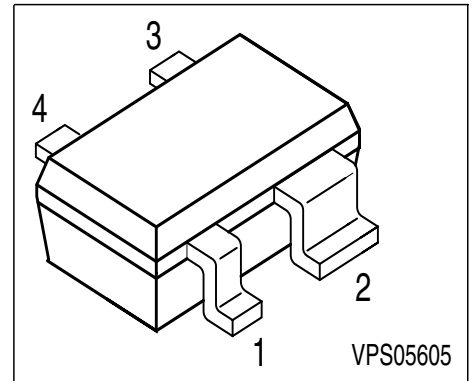**NPN Silicon RF Transistor***

- For low voltage / low current applications
- Ideal for VCO modules and low noise amplifiers
- Low noise figure: 1.1 dB at 1.8 GHz
- Excellent ESD performance
- High f_T of 22 GHz

* Short-term description

VPS05605

ESD: **E**lectro**s**tatic **d**ischarge sensitive device, observe handling precaution!

Type	Marking	Pin Configuration						Package
BFP460	ABs	1 = E	2 = C	3 = E	4=B	-	-	SOT343

Maximum Ratings

Parameter	Symbol	Value	Unit
Collector-emitter voltage	V_{CEO}		V
$T_A > 0\,°C$		4.5	
$T_A \leq 0\,°C$		4.2	
Collector-emitter voltage	V_{CES}	15	
Collector-base voltage	V_{CBO}	15	
Emitter-base voltage	V_{EBO}	1.5	
Collector current	I_C	50	mA
Base current	I_B	5	
Total power dissipation[1)2)]	P_{tot}	200	mW
$T_S \leq 100°C$			
Junction temperature	T_i	150	°C
Ambient temperature	T_A	-65 ... 150	
Storage temperature	T_{stg}	-65 ... 150	

Thermal Resistance

Parameter	Symbol	Value	Unit
Junction - soldering point[3)]	R_{thJS}	≤ 250	K/W

[1]P_{tot} due to Maximum Ratings

[2]T_S is measured on the collector lead at the soldering point to the pcb

[3]For calculation of R_{thJA} please refer to Application Note Thermal Resistance

Jun-14-2004

Electrical Characteristics at T_A = 25°C, unless otherwise specified

Parameter	Symbol	Values			Unit
		min.	typ.	max.	
DC Characteristics					
Collector-emitter breakdown voltage I_C = 1 mA, I_B = 0	$V_{(BR)CEO}$	4.5	5.8	-	V
Collector-base cutoff current V_{CB} = 5 V, I_E = 0	I_{CBO}	-	-	100	nA
Emitter-base cutoff current V_{EB} = 0,5 V, I_C = 0	I_{EBO}	-	-	1	µA
DC current gain I_C = 20 mA, V_{CE} = 3 V, pulse measured	h_{FE}	90	120	160	-

Jun-14-2004

Electrical Characteristics at T_A = 25°C, unless otherwise specified

Parameter	Symbol	Values			Unit
		min.	typ.	max.	
AC Characteristics (verified by random sampling)					
Transition frequency I_C = 30 mA, V_{CE} = 3 V, f = 1 GHz	f_T	16	22	-	GHz
Collector-base capacitance V_{CB} = 3 V, f = 1 MHz, emitter grounded	C_{cb}	-	0.32	0.45	pF
Collector emitter capacitance V_{CE} = 3 V, f = 1 MHz, base grounded	C_{ce}	-	0.28	-	
Emitter-base capacitance V_{EB} = 0.5 V, f = 1 MHz, collector grounded	C_{eb}	-	0.55	-	
Noise figure I_C = 5 mA, V_{CE} = 3 V, Z_S = Z_{Sopt} , f = 1.8 GHz	F	-	1.1	-	dB
I_C = 5 mA, V_{CE} = 3 V, Z_S = Z_{Sopt} , f = 3 GHz		-	1.35	-	
Power gain, maximum stable[1] I_C = 20 mA, V_{CE} = 3 V, Z_S = Z_{Sopt}, Z_L = Z_{Lopt}, f = 1.8 GHz	G_{ms}	-	17.5	-	dB
Power gain, maximum available[1] I_C = 20 mA, V_{CE} = 3 V, Z_S = Z_{Sopt}, Z_L = Z_{Lopt} , f = 3 GHz	G_{ma}	-	12.5	-	dB
Transducer gain I_C = 20 mA, V_{CE} = 3 V, Z_S = Z_L = 50Ω, f = 1,8 GHz	$|S_{21e}|^2$	-	15	-	dB
I_C = 20 mA, V_{CE} = 3 V, Z_S = Z_L = 50Ω , f = 3 GHz		-	10.5	-	
Third order intercept point at output[2] V_{CE} = 3 V, I_C = 20 mA, f = 1.8 GHz	IP_3	-	27.5	-	dBm
1dB Compression point at output I_C = 20 mA, V_{CE} = 3 V, f = 1.8 GHz	P_{-1dB}	-	11.5	-	

[1]G_{ma} = $|S_{21} / S_{12}|$ $(k-(k^2-1)^{1/2})$, G_{ms} = $|S_{21} / S_{12}|$

[2]IP3 value depends on termination of all intermodulation frequency components.
Termination used for this measurement is 50Ω from 0.1 MHz to 6 GHz
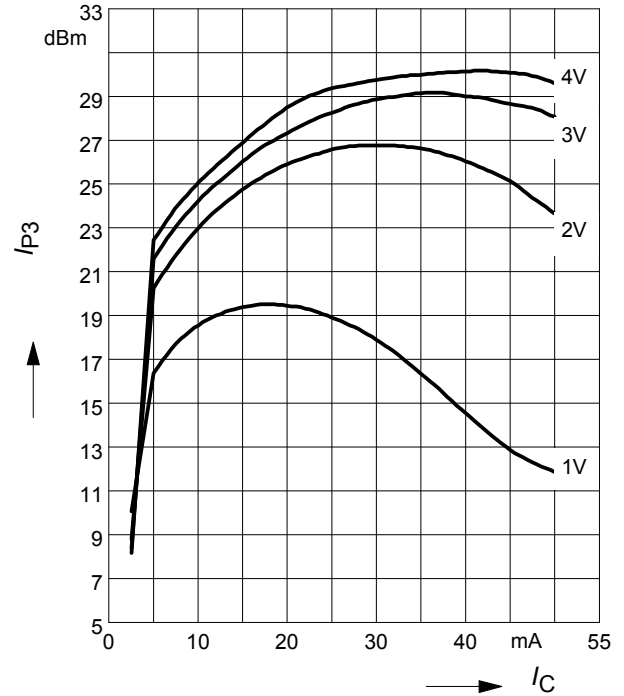
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Collector-base capacitance $C_{cb} = f(V_{CB})$

f = 1MHz

Third order Intercept Point $IP_3 = f(I_C)$

(Output, $Z_S = Z_L = 50\Omega$)

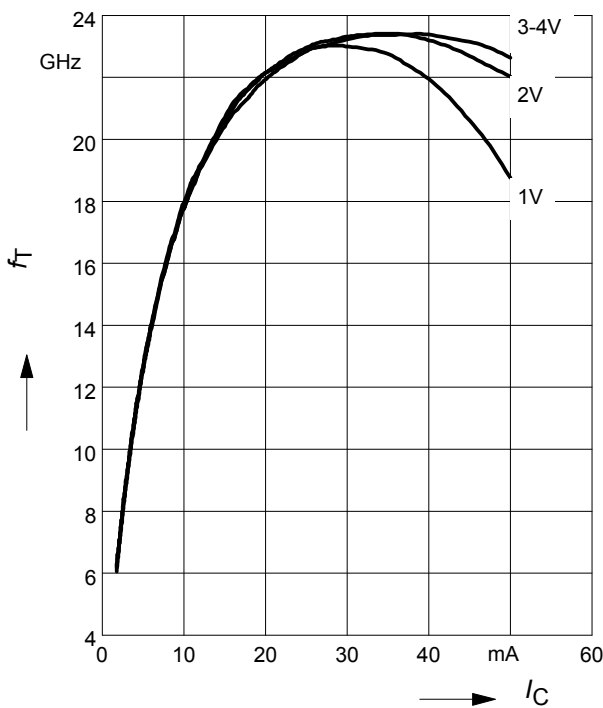V_{CE} = parameter, f = 1800MHz -
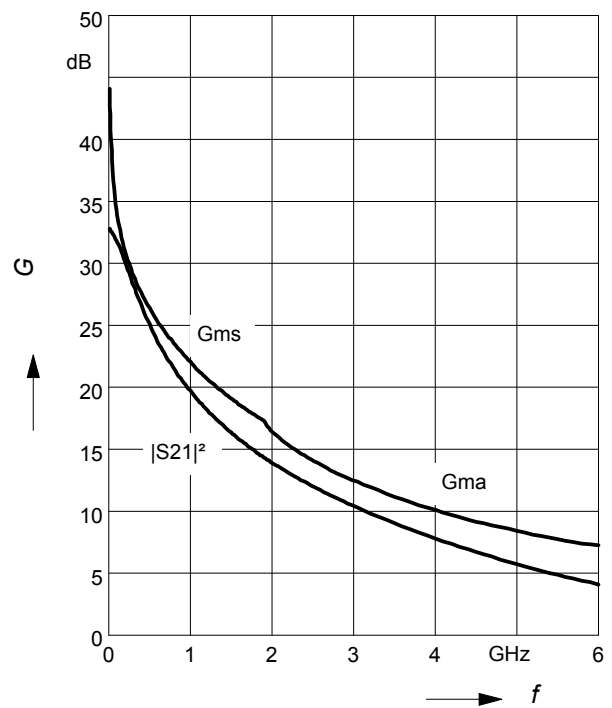

Transition frequency $f_T = f(I_C)$

f = 1 GHz

V_{CE} = parameter in V
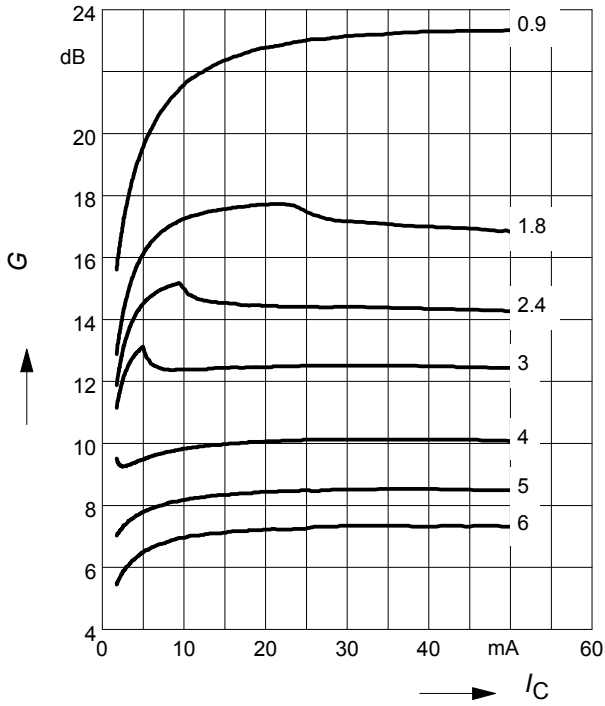

Power gain G_{ma}, G_{ms}, $|S_{21}|^2 = f(f)$

V_{CE} = 3 V, I_C = 20 mA

Jun-14-2004

Power gain G_{ma}, G_{ms} = f (I_C)

V_{CE} = 3V

f = parameter in GHz

Power gain G_{ma}, G_{ms} = f (V_{CE})

I_C = 20 mA

f = parameter in GHz

Jun-14-2004